NPN RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TP62601** is a Common Collector Device Designed for Applications up to 3.0 GHz Band.

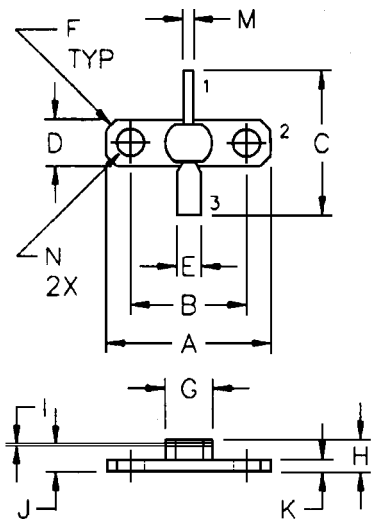
FEATURES INCLUDE:

- Hermetic Package
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	0.5 A
V_{CBO}	45 V
P_{DISS}	11.6 W @ T_C = 25 °C
T_J	-55 °C to+200 °C
T_{STG}	-55 °C to+200 °C
θ_{JC}	15 °C/W

PACKAGE STYLE 230 2L FLG



DIM	MILLIMETER	TOL	INCHES	TOL
A	20.32	.13	.800	.005
B	14.27	.13	.562	.005
C	18.03	MIN	.710	MIN
D	5.84	.13	.230	.005
E	3.05	.13	.120	.005
F	1.27 x 45°	.13	.005x45°	.005
G	5.84	.13	.230	.005
H	4.57	REF	.180	REF
I	0.13	.02	.005	.001
J	3.30	.13	.130	.005
K	1.52	.13	.060	.005
M	1.27	.13	.050	.005
N	3.30 DIA	.13	.130 DIA	.005

1 = EMITTER 2 = COLLECTOR
3 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 1.0 mA	45			V
BV_{CER}	I_C = 20 mA R_{BE} = 10 Ω	50			V
BV_{CEO}	I_C = 20 mA	22			V
BV_{EBO}	I_E = 250 µA	3.5			V
I_{CBO}	V_{CB} = 28 V			125	µA
h_{FE}	V_{CE} = 5.0 V I_C = 100 mA	20		120	---
C_{OB}	V_{CB} = 28 V f = 1.0 MHz			5.0	pF
P_{OUT}	V_{CE} = 20 V I_E = 220 mA f = 2.0 GHz	1.25			W
f_t	V_{CE} = 20 V I_E = 220 mA		2.7		GHz